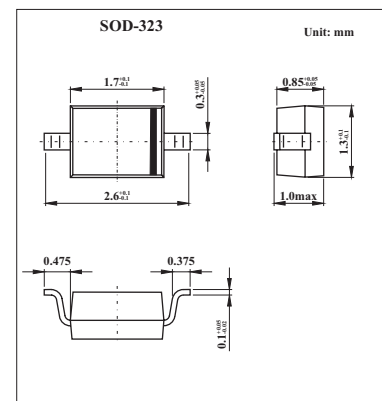


Schottky Barrier Diodes

1N5819WS

■ Features

- Power Dissipation: $P_D = 200\text{mW}$
- Collector Current: $I_F = 1\text{A}$
- Collector-Base Voltage: $V_R = 40\text{V}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector Current	I_F	1	A
Collector-Base Voltage	V_R	40	V
Power Dissipation	P_D	200	mW
Operating and Storage Junction Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 1\text{mA}$	40			V
Forward Voltage	V_F	$I_F = 0.1\text{A}$			0.45	V
		$I_F = 1\text{A}$			0.6	
		$I_F = 3\text{A}$			0.9	
Reverse Voltage Leakage Current	I_R	$V_R = 40\text{V}$			1	mA
		$V_R = 4\text{V}$			0.05	
		$V_R = 6\text{V}$			0.075	
Diode Capacitance	C_D	$V_R = 4\text{V}, f = 1.0\text{MHz}$			120	pF

■ Marking

Marking	SL
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